

CNZ1120 (ON1120)

Photo Interrupter

For contactless SW, object detection

Overview

CNZ1120 is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

Features

- Wide gap between emitting and detecting elements, suitable for thick plate detection Gap: 10 mm
- Fast response: t_r , t_f = 6 μ s (typ.)
- The external case is molded using visible light cutoff resin. The case has no openings, so the photosensor is not easily susceptible to output attenuation resulting from dust or particles

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Input (Light emitting diode)	Reverse voltage	V_R	3	V
	Forward current	I_F	50	mA
	Power dissipation *1	P_D	75	mW
Output (Photo transistor)	Collector-emitter voltage (Base open)	V_{CEO}	20	V
	Emitter-collector voltage (Base open)	V_{ECO}	5	V
	Collector current	I_C	20	mA
	Collector power dissipation *2	P_C	100	mW
Temperature	Operating ambient temperature	T_{opr}	-5 to +60	$^\circ\text{C}$
	Storage temperature	T_{stg}	-15 to +65	$^\circ\text{C}$

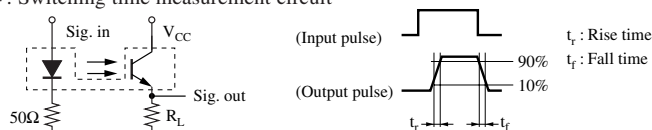
Electrical-Optical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

	Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input characteristics	Forward voltage	V_F	$I_F = 50 \text{ mA}$		1.2	1.5	V
	Reverse current	I_R	$V_R = 3 \text{ V}$			10	μA
Output characteristics	Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10 \text{ V}$, $I_F = 0 \text{ mA}$, $I_D = 0 \text{ mA}$			200	nA
	Collector-emitter capacitance	C_C	$V_{CE} = 10 \text{ V}$, $f = 1 \text{ MHz}$		5		pF
Transfer characteristics	Collector current	I_C	$V_{CE} = 10 \text{ V}$, $I_F = 20 \text{ mA}$, $R_L = 100 \Omega$	1.0			mA
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_F = 50 \text{ mA}$, $I_C = 0.1 \text{ mA}$			0.4	V
	Rise time *	t_r	$V_{CC} = 10 \text{ V}$, $I_C = 1 \text{ mA}$, $R_L = 100 \Omega$		6		μs
	Fall time *	t_f			6		μs

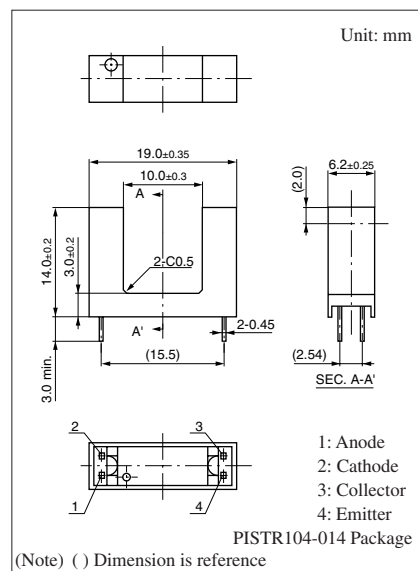
Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarded radiation.

3. *: Switching time measurement circuit



Note) The part number in the parenthesis shows conventional part number.



Note) *1: Input power derating ratio is 1.88 mW/ $^\circ\text{C}$ at $T_a \geq 25^\circ\text{C}$.

*2: Output power derating ratio is 2.50 mW/ $^\circ\text{C}$ at $T_a \geq 25^\circ\text{C}$.

Caution for Safety

 **DANGER**

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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